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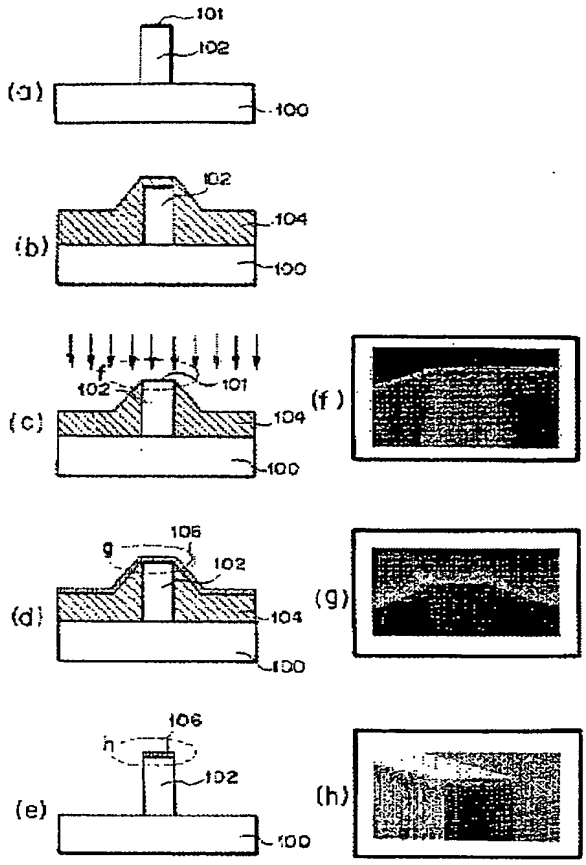
TITLE : METHOD FOR FABRICATING SEMICONDUCTOR ELEMENT, SEMICONDUCTOR ELEMENT, AND GYRO



ABSTRACT : PROBLEM TO BE SOLVED: To provide a method for fabricating a semiconductor element in which an electrode can be formed easily on the upper surface of micro protrusions and a method for fabricating a semiconductor element in which a protective film can be formed easily on the side face of the semiconductor element having a protrusion area on a substrate.

SOLUTION: A member having a protrusion 102 of a desired height is prepared on a substrate 100 as shown on fig. (a). The protrusion 102 is then buried using a burying material 104 such that the burying material is thinner on the upper surface of the protrusion than other parts as shown on fig. (b). Subsequently, the burying material is etched uniformly from above to expose the upper surface 101 of the protrusion as shown on fig. (c). Thereafter, an electrode material 106 is deposited on the entire surface of the substrate as shown on fig. (d). Finally, the electrode material is removed along with the burying material except the upper surface of the protrusion, i.e., so-called lift-off is performed, as shown on fig. (e) thus forming a structure having an electrode on the upper surface of a protrusion while self-aligning.